

Silicon N Channel MOS Type (U-MOSⅢ)/Silicon Epitaxial Schottky Barrier Diode

# SSM5H05TU

## DC-DC Converter

- Combined Nch MOSFET and Schottky Diode in one package.
- Low RDS (ON) and low VF

### Maximum Ratings (Ta = 25°C) MOSFET

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	$V_{DS}$	20	V
Gate-Source voltage	$V_{GSS}$	$\pm 12$	V
Drain current	DC	$I_D$	1.5
	Pulse	$I_{DP}$ (Note 2)	6.0
Drain power dissipation	$P_D$ (Note 1)	0.5	W
	$t = 10s$	0.8	
Channel temperature	$T_{ch}$	150	°C

### Maximum Ratings (Ta = 25°C) SCHOTTKY DIODE

Characteristics	Symbol	Rating	Unit
Maximum (peak) reverse voltage	$V_{RM}$	15	V
Reverse voltage	$V_R$	12	V
Average forward current	$I_O$	0.5	A
Peak one cycle surge forward current (non-repetitive)	$I_{FSM}$	2 (50 Hz)	A
Junction temperature	$T_j$	125	°C

### Maximum Ratings (Ta = 25°C) MOSFET, DIODE COMMON

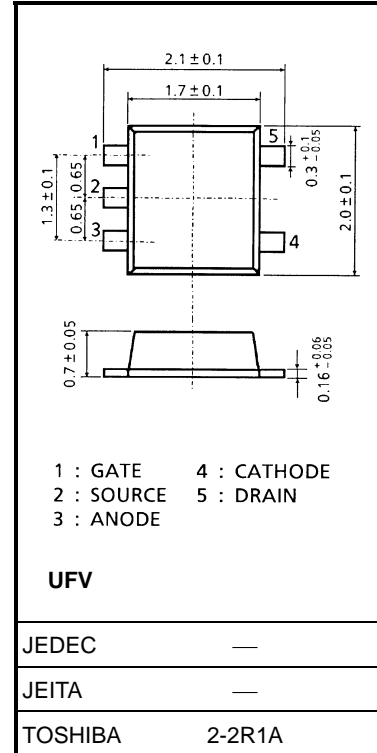
Characteristics	Symbol	Rating	Unit
Storage temperature	$T_{stg}$	-55~125	°C
Operating temperature	$T_{opr}$ (Note 3)	-40~85	°C

Note 1: Mounted on FR4 board  
(25.4 mm × 25.4 mm × 1.6 t, Cu pad: 645 mm<sup>2</sup>)

Note 2: The pulse width is limited by max channel temperature.

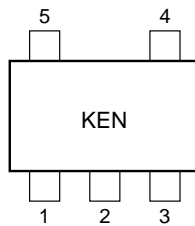
Note 3: The operating temperature is limited by max channel temperature and max junction temperature.

Unit: mm

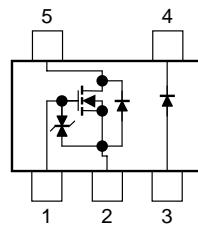


Weight: 7 mg (typ.)

## Marking



## Equivalent Circuit



## Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing and use containers and other objects that are made of anti-static materials.

The Channel-to-Ambient thermal resistance  $R_{th(ch-a)}$  and the drain power dissipation  $P_D$  vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

## MOSFET

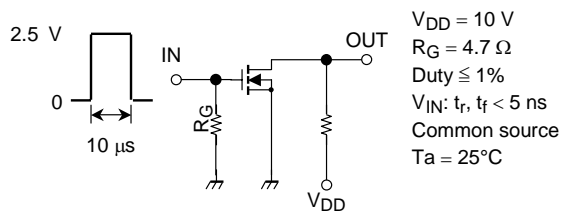
### Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0$	—	—	$\pm 1$	$\mu\text{A}$
Drain-Source breakdown voltage	$V_{(BR) DSS}$	$I_D = 1\text{ mA}, V_{GS} = 0$	20	—	—	V
	$V_{(BR) DSX}$	$I_D = 1\text{ mA}, V_{GS} = -12\text{ V}$	12	—	—	
Drain Cut-off current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0$	—	—	1	$\mu\text{A}$
Gate threshold voltage	$V_{th}$	$V_{DS} = 3\text{ V}, I_D = 0.1\text{ mA}$	0.4	—	1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 0.75\text{ A}$ (Note 4)	1.4	2.8	—	S
Drain-Source ON resistance	$R_{DS(ON)}$	$I_D = 0.75\text{ A}, V_{GS} = 4\text{ V}$ (Note 4)	—	140	160	m $\Omega$
		$I_D = 0.75\text{ A}, V_{GS} = 2.5\text{ V}$ (Note 4)	—	180	220	
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	125	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	17	—	pF
Output capacitance	$C_{oss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	42	—	pF
Switching time	Turn-on time	$t_{on}$	$V_{DD} = 10\text{ V}, I_D = 0.75\text{ A}$		—	ns
	Turn-off time	$t_{off}$	$V_{GS} = 0 \sim 2.5\text{ V}, R_G = 4.7\ \Omega$		—	

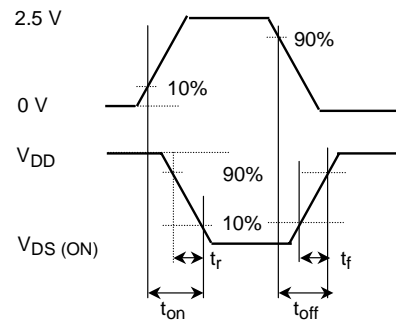
Note 4: Pulse measurement

### Switching Time Test Circuit

#### (a) Test circuit



#### (b) $V_{IN}$



#### (c) $V_{OUT}$

### Precaution

$V_{th}$  can be expressed as the voltage between gate and source when the low operating current value is  $I_D = 100\ \mu\text{A}$  for this product. For normal switching operation,  $V_{GS(ON)}$  requires a higher voltage than  $V_{th}$  and  $V_{GS(OFF)}$  requires a lower voltage than  $V_{th}$ . (The relationship can be established as follows:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .)

Please take this into consideration when using the device. The  $V_{GS}$  recommended voltage for turning on this product is 2.5V or higher.

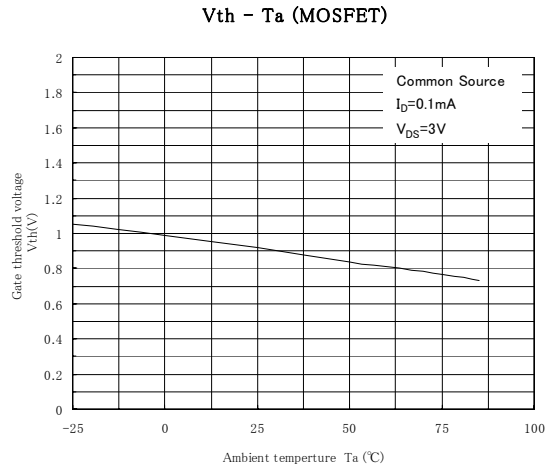
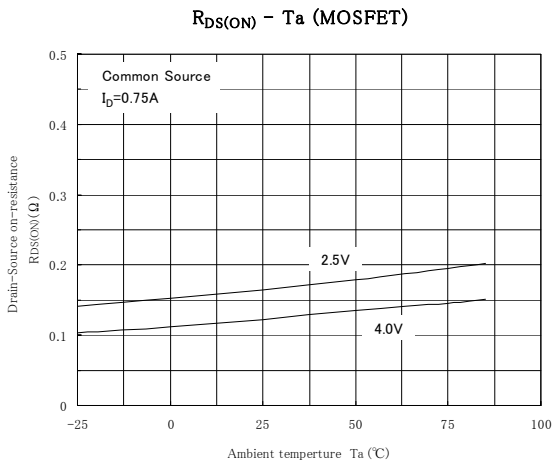
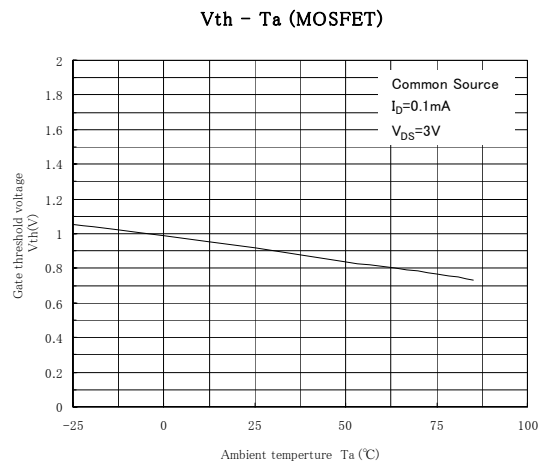
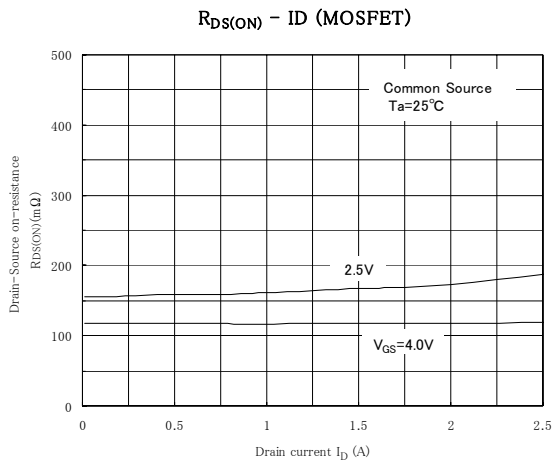
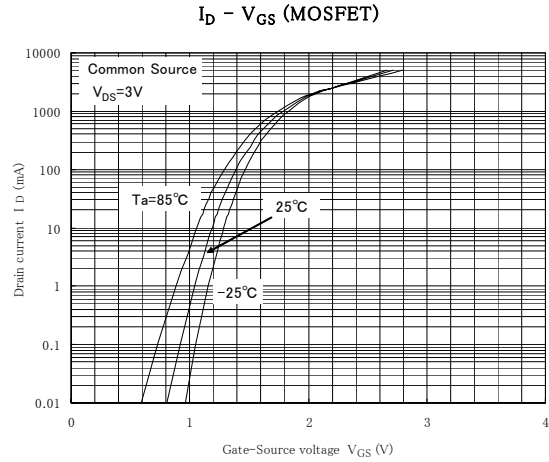
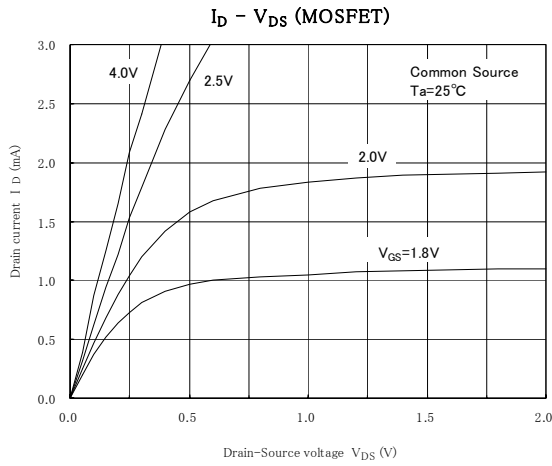
**Schottky Diode****Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F (1)$	$I_F = 0.3 \text{ A}$	—	0.33	0.39	V
	$V_F (2)$	$I_F = 0.5 \text{ A}$	—	0.37	0.43	V
Reverse current	$I_R$	$V_R = 12 \text{ V}$	—	—	100	$\mu\text{A}$
Total capacitance	$C_T$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	—	80	—	pF

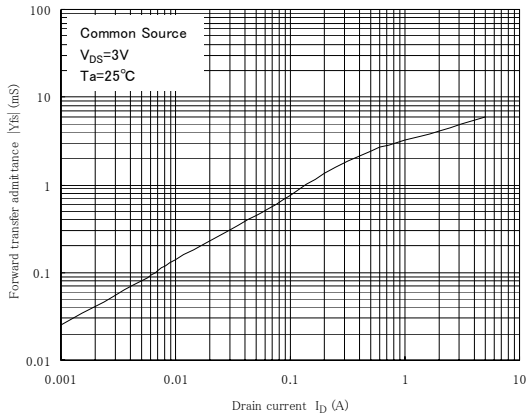
**Precaution**

The schottky barrier diode of this product has large reverse current leakage characteristics compared to other switching diodes. This current leakage, combined with improper operating temperature or voltage, may cause thermal runaway. Be sure to take forward and reverse loss into consideration during you design.

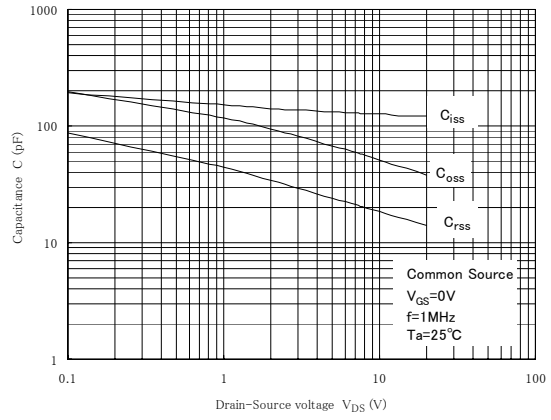
## MOSFET Electrical Characteristics



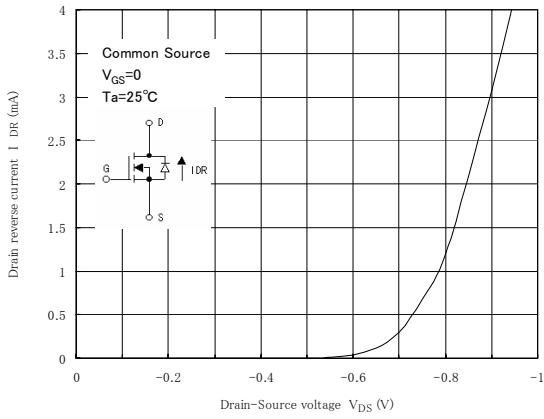
**$|Y_{fs}| - I_D$  (MOSFET)**



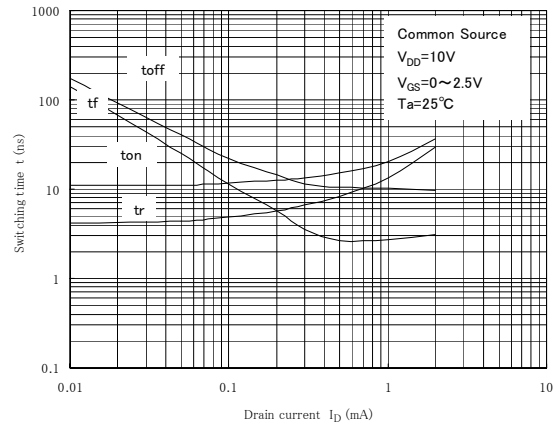
**C -  $V_{DS}$  (MOSFET)**



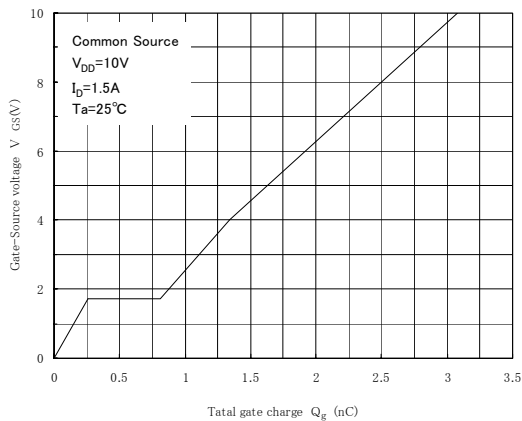
**$I_{DR} - V_{DS}$  (MOSFET)**



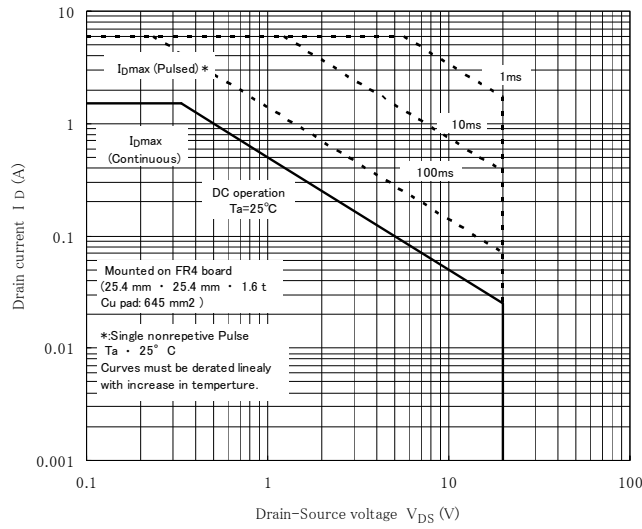
**t -  $I_D$  (MOSFET)**



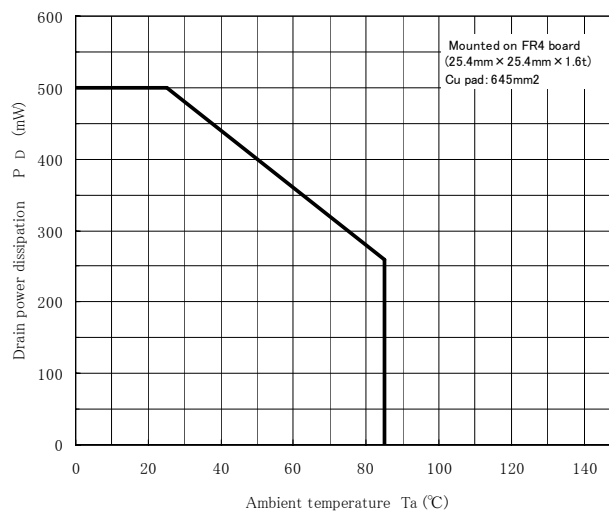
**Dynamic Input Characteristic (MOSFET)**



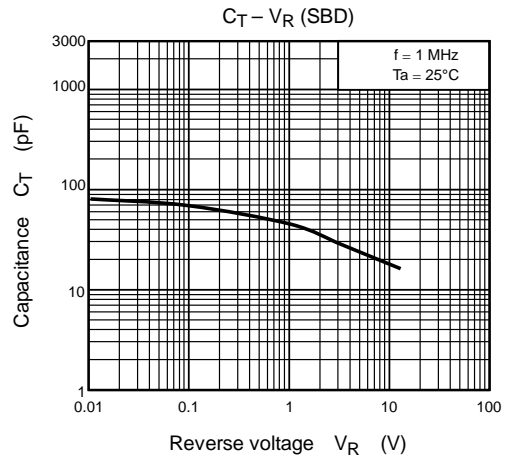
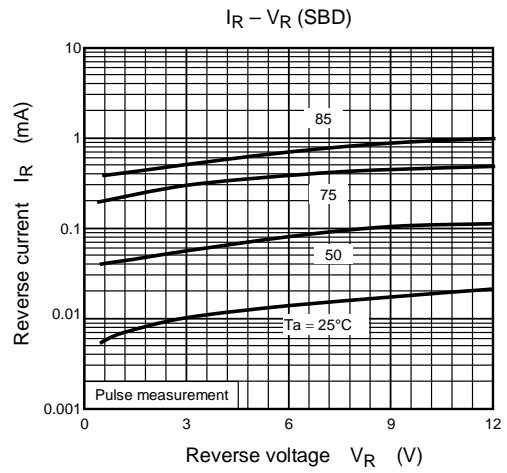
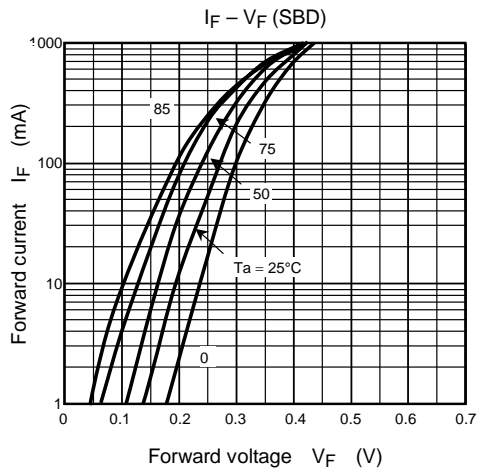
**Safe operating area (MOSFET)**



**$P_D - T_a$  (MOSFET)**

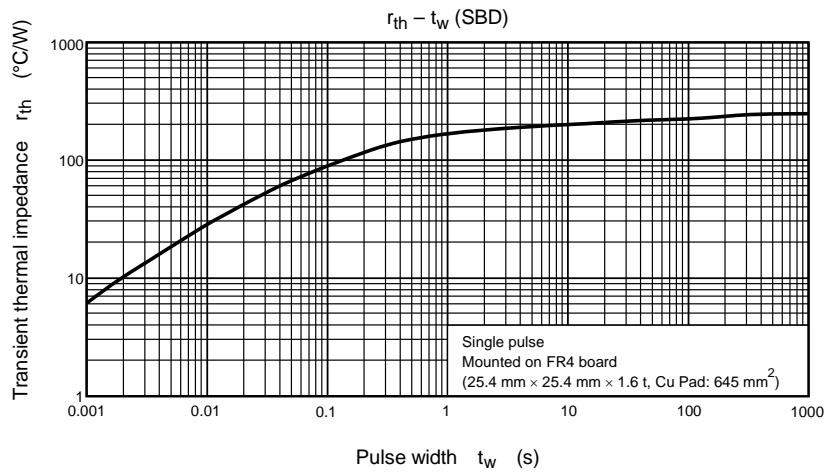
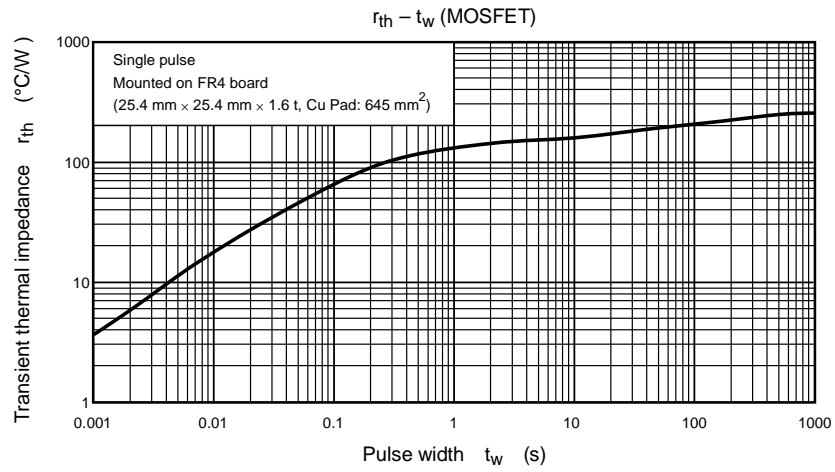


## SBD Electrical Characteristics





**Transient Thermal Impedance**



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